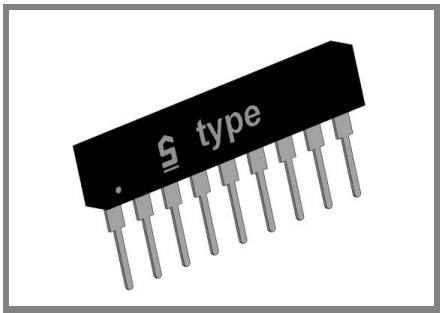
DA 811AK ... 8110AK 1,2W ...



Diode arrays

Silicon rectifiers arrays

DA 811AK ... 8110AK 1,2W

Forward Current: 0,6 A

Reverse Voltage: 100 to 1000 V

Publish Data

Features

Mechanical Data

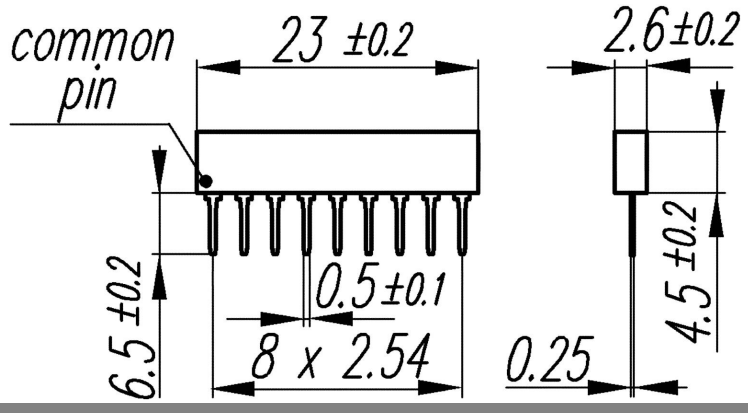
- 9 Pin - plastic case
- Terminals: plated terminals solderable per IEC 68-2-20
- Mounting position : any
- Weigh approx. 0,6 g
- Standard packing : bulk
- DA 811A ... DA 8110A - common anodes
- DA 811K ... DA 8110K - common cathodes
- 1) Valid for one branch; per diode for simultaneous operation I_{FAV} = 150 mA
- 2) I_F = 1A, T_A = 25ºC

Type	Repetitive peak reverse voltage V_{RRM} V	Surge peak reverse voltage V_{RSM} V	Max. reverse recovery time I_F = A I_R = A I_{RR} = A t_{rr} ns	Max. forward voltage V_F 2)
DA 811A/K	100	120	/	1,1
DA 814A/K	400	480	/	1,1
DA 8110A/K	1000	1200	/	1,1

Absolute Maximum Ratings	T_c = 25ºC unless otherwise specified		
Symbol	**Conditions**	**Values**	**Units**
I_{FAV}	Max. averaged fwd. current, R-load, T_A = 25 °C 1)	0,6	A
I_{FRM}	Repetitive peak forward current f > 15 Hz 1)	6	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave 3)	30	A
i²t	Rating for fusing, t < 10 ms 3)	4,5	A²s
R_{thA}	Max. thermal resistance junction to ambient 1)	85	K/W
R_{thT}	Max. thermal resistance junction to terminals 1)	/	K/W
T_j	Operating junction temperature	-50 ... +150	°C
T_s	Storage temperature	-50 ... +150	°C

Characteristics	T_c = 25ºC unless otherwise specified		
Symbol	**Conditions**	**Values**	**Units**
I_R	Maximum leakage current, T_j = 25 °C; V_R = V_{RRM}	< 10	µA
	T_j = 100 °C; V_R = V_{RRM}	< 90	µA
C_J	Typical junction capacitance (at MHz and applied reverse voltage of V)	/	pF
Q_{rr}	Reverse recovery charge (U_R = V; I_F = A; dI_F/dt = A/ms)	/	µC
E_{RSM}	Non repetitive peak reverse avalanche energy (I_R = mA; T_j = °C; inductive load switched off)		mJ

Dimensions in mm



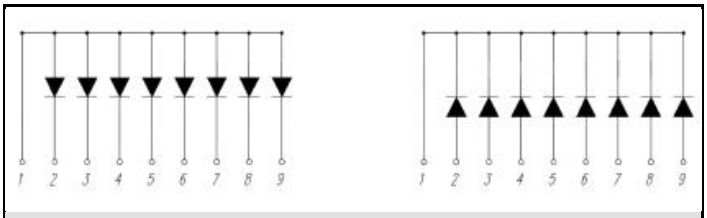


Fig. 1 : DA 811A ... DA 8110A; DA 811K ... DA 8110K

